

SEMITOP[®] 3

3-phase bridge rectifier + brake chopper +3-phase bridge inverter SK 15 DGDL 126 ET

Preliminary Data

Features

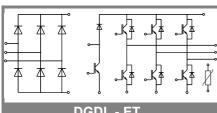
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench technology IGBT
- CAL High Density FWD
- Integrated NTC temperature sensor

Typical Applications*

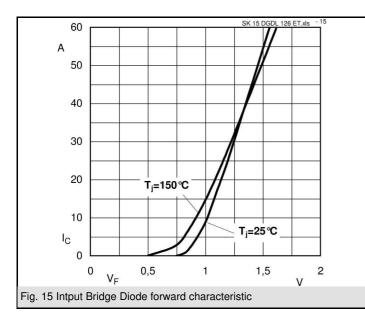
Inverter

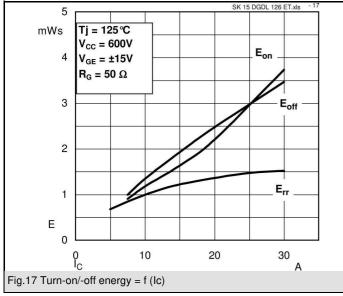
Absolute Maximum Ratings		T_s = 25°C, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V _{CES}		1200	V				
Ι _C	T _s = 25 (80) °C	22 (15)	А				
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	30	А				
V _{GES}		±20	V				
Т _ј		-40 +150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (80) °C	25 (17)	А				
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	30	А				
Т _ј		-40 +150	°C				
Rectifier							
V _{RRM}		1600	V				
I _F	T _s = 80 °C	21	А				
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	220	А				
l ² t	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	240	A²s				
Т _ј		-40 +150	°C				
T _{sol}	Terminals, 10s	260	°C				
T _{stg}		-40 +125	°C				
V _{isol}	AC, 1 min. / 1s	2500 / 3000	V				

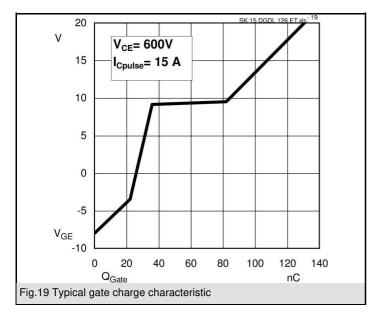
Characteristics		T _s = 25°C	T_s = 25°C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CEsat}	I _C = 15 A, T _i = 25 (125) °C		1,7 (2)	2,1	V				
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 0,6 \text{ mA}$	5	5,8	6,5	V				
V _{CE(TO)}	T _j = 25 °C (125) °C		1 (0,9)		V				
r _T	$T_{j} = 25 \ ^{\circ}C \ (125) \ ^{\circ}C$		45 (70)		mΩ				
Cies	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		1,2		nF				
C _{oes}	V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz		0,1		nF				
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		9,1		nF				
R _{th(j-s)}	per IGBT			1,6	K/W				
t _{d(on)}	under following conditions		25		ns				
t _r	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		25		ns				
t _{d(off)}	I _C = 15 A, T _j = 125 °C		385		ns				
t _f	$R_{Gon} = R_{Goff} = 30 \ \Omega$		90		ns				
E _{on}	inductive load		2		mJ				
E _{off}			1,8		mJ				
Diode - Ir	verter, Chopper								
$V_F = V_{EC}$	I _F = 15 A, T _j = 25(125) °C		1,6 (1,6)		V				
V _(TO)	T _j = 25 °C (125) °C		1 (0,8)		V				
r _T	T _j = 25 °C (125) °C		40 (53)		mΩ				
$R_{th(j-s)}$	per diode			2,1	K/W				
I _{RRM}	under following conditions		25		Α				
Q _{rr}	I _F = 15 A, V _R = 600 V		3		μC				
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		1,1		mJ				
	di _{F/dt} = 900 A/µs								
Diode rec	tifier								
V _F	I _F = 15 A, T _i = 25() °C		1,1		V				
V _(TO)	T _i = 150 °C		0,9		V				
r _T	T _j = 150 °C		20		mΩ				
R _{th(j-s)}	per diode			2	K/W				
	tur sensor								
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω				
Mechanic	al data	I							
w			30		g				
M _s	Mounting torque			2,5	Nm				

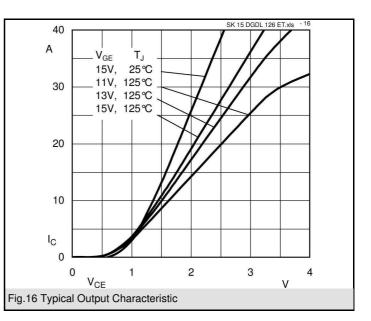


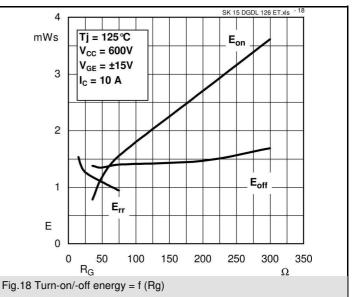
DGDL - ET

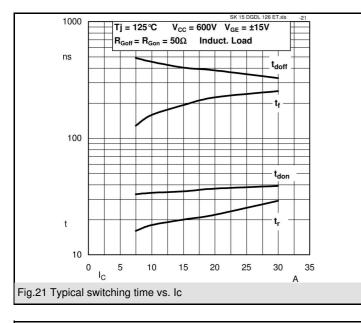


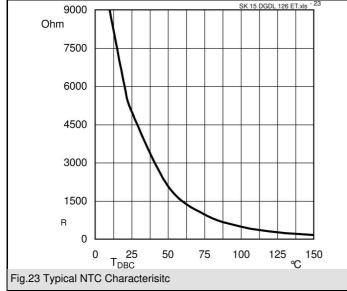


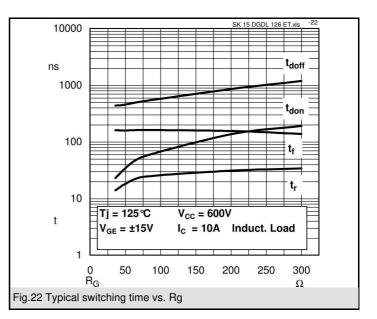


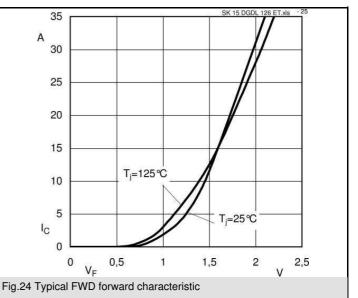


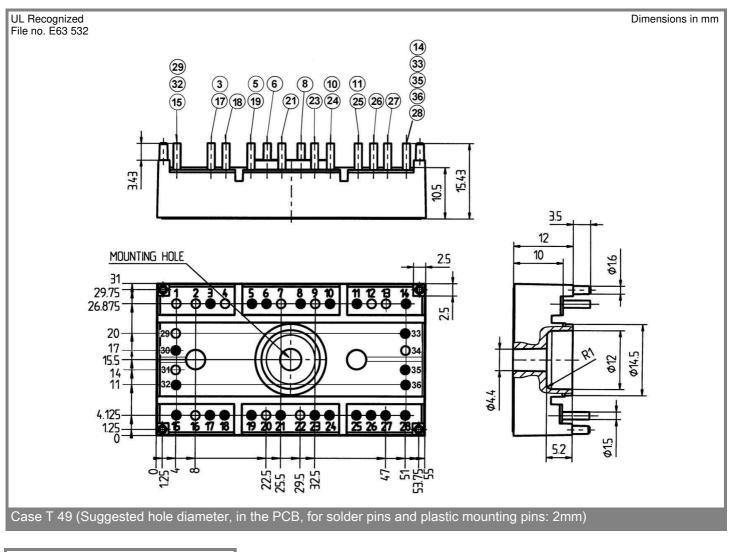


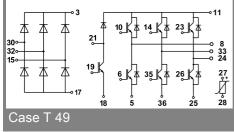












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.